



# PSMN6R7-40MSD

N-channel 40 V, 6.7 mΩ, standard level MOSFET in LPAK33 using NextPower-S3 technology

11 November 2019

Product data sheet

## 1. General description

50 A, standard level N-channel enhancement mode MOSFET in 175 °C LPAK33 package using advanced TrenchMOS Superjunction technology. This product has been designed and qualified for high efficiency applications at high switching frequencies.

## 2. Features and benefits

- Avalanche rated, 100% tested
- NextPower-S3 technology delivers 'superfast switching with soft body-diode recovery'
- Low  $Q_{rr}$ ,  $Q_G$  and  $Q_{GD}$  for high system efficiency, especially at high switching frequencies
- Low spiking and ringing for low EMI designs
- High reliability clip bonded and solder die attach Mini Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Exposed leads can be wave soldered, visual solder joint inspection and high quality solder joints
- Low parasitic inductance and resistance

## 3. Applications

- Secondary side synchronous rectification
- DC-to-DC converters
- Brushless DC motor drive
- LED lighting

## 4. Quick reference data

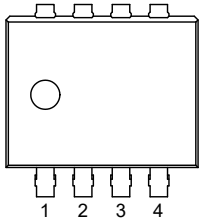
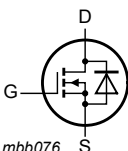
Table 1. Quick reference data

| Symbol                         | Parameter                        | Conditions                                                                                                                |     | Min | Typ | Max | Unit |
|--------------------------------|----------------------------------|---------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|-----|------|
| $V_{DS}$                       | drain-source voltage             | $25\text{ °C} \leq T_j \leq 175\text{ °C}$                                                                                |     | -   | -   | 40  | V    |
| $I_D$                          | drain current                    | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>                                                 | [1] | -   | -   | 50  | A    |
| $P_{tot}$                      | total power dissipation          | $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>                                                                          |     | -   | -   | 65  | W    |
| $T_j$                          | junction temperature             |                                                                                                                           |     | -55 | -   | 175 | °C   |
| <b>Static characteristics</b>  |                                  |                                                                                                                           |     |     |     |     |      |
| $R_{DS(on)}$                   | drain-source on-state resistance | $V_{GS} = 10\text{ V}$ ; $I_D = 20\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>                             |     | -   | 5.7 | 6.7 | mΩ   |
| <b>Dynamic characteristics</b> |                                  |                                                                                                                           |     |     |     |     |      |
| $Q_{GD}$                       | gate-drain charge                | $I_D = 20\text{ A}$ ; $V_{DS} = 20\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a> |     | 0.7 | 2.4 | 4.8 | nC   |
| $Q_{G(tot)}$                   | total gate charge                |                                                                                                                           |     | 10  | 16  | 22  | nC   |

[1] 50A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline                                                                                    | Graphic symbol                                                                                |
|-----|--------|-----------------------------------|-------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------|
| 1   | S      | source                            | <br>LPAK33 (SOT1210) | <br>mbb076 |
| 2   | S      | source                            |                                                                                                       |                                                                                               |
| 3   | S      | source                            |                                                                                                       |                                                                                               |
| 4   | G      | gate                              |                                                                                                       |                                                                                               |
| mb  | D      | Mounting base; connected to drain |                                                                                                       |                                                                                               |

## 6. Ordering information

Table 3. Ordering information

| Type number   | Package |                                                                                |         |
|---------------|---------|--------------------------------------------------------------------------------|---------|
|               | Name    | Description                                                                    | Version |
| PSMN6R7-40MSD | LPAK33  | Plastic, single ended surface mounted package (LPAK33); 8 leads; 0.65 mm pitch | SOT1210 |

## 7. Marking

Table 4. Marking codes

| Type number   | Marking code |
|---------------|--------------|
| PSMN6R7-40MSD | 6D7S40       |

## 8. Limiting values

Table 5. Limiting values

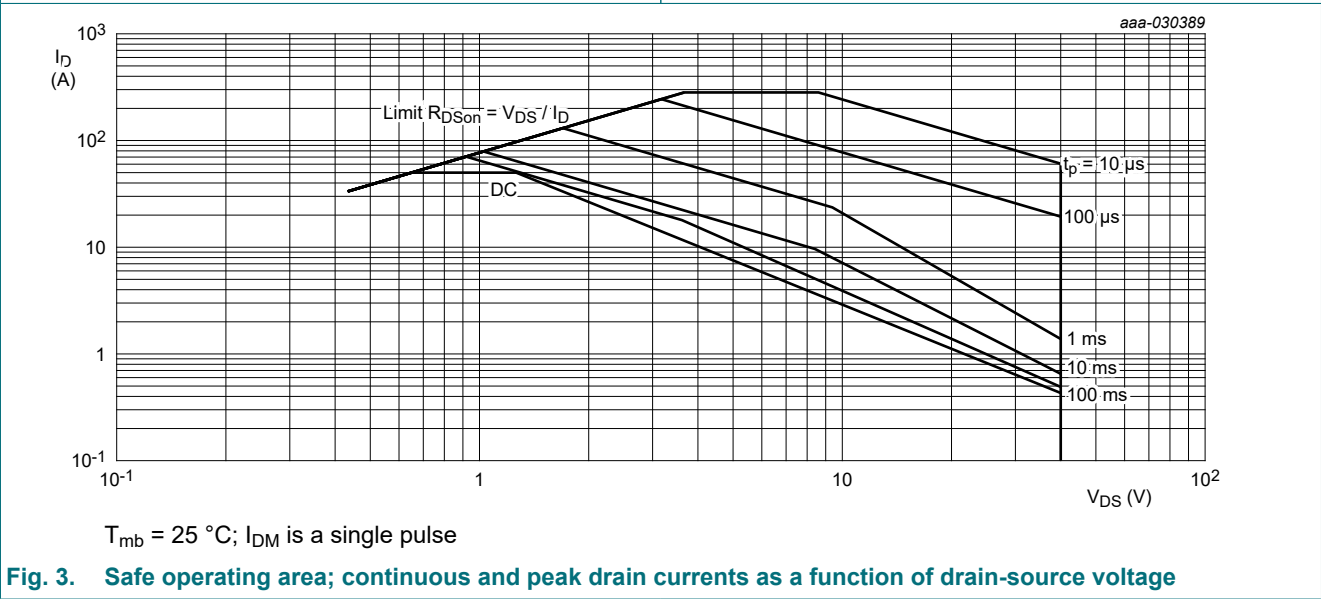
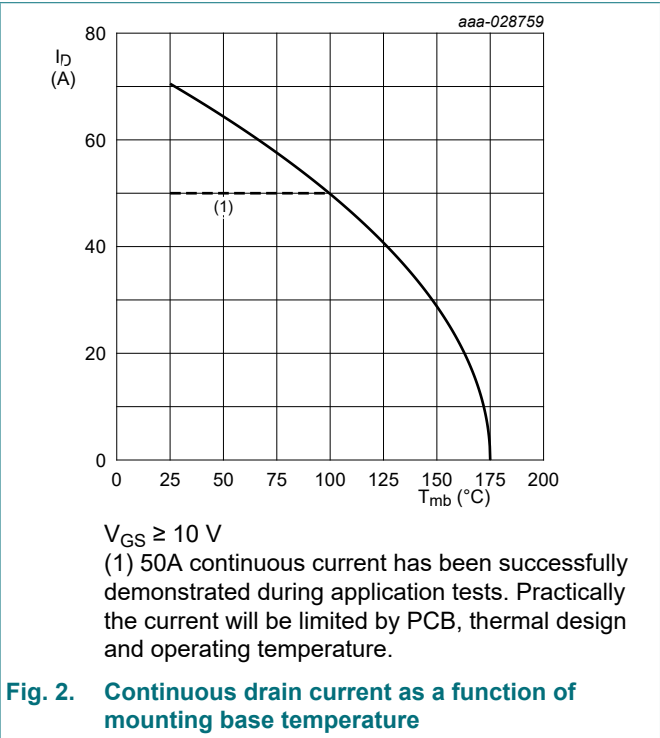
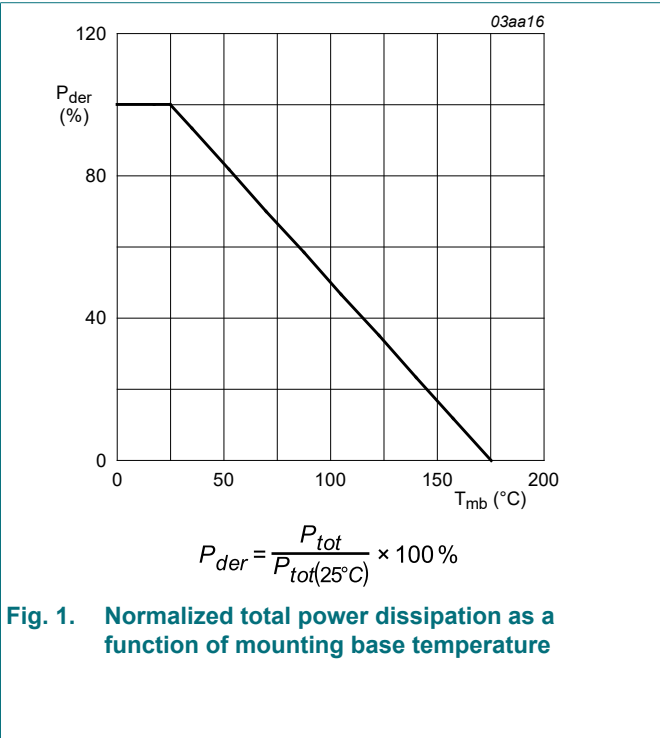
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                    | Parameter                  | Conditions                                                                                   |     | Min | Max | Unit |
|---------------------------|----------------------------|----------------------------------------------------------------------------------------------|-----|-----|-----|------|
| $V_{DS}$                  | drain-source voltage       | $25\text{ °C} \leq T_j \leq 175\text{ °C}$                                                   |     | -   | 40  | V    |
| $V_{DSM}$                 | peak drain-source voltage  | $t_p \leq 20\text{ ns}$ ; $f \leq 500\text{ kHz}$ ; $E_{DS(AL)} \leq 200\text{ nJ}$ ; pulsed |     | -   | 45  | V    |
| $V_{DGR}$                 | drain-gate voltage         | $25\text{ °C} \leq T_j \leq 175\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$                    |     | -   | 40  | V    |
| $V_{GS}$                  | gate-source voltage        |                                                                                              |     | -20 | 20  | V    |
| $P_{tot}$                 | total power dissipation    | $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>                                             |     | -   | 65  | W    |
| $I_D$                     | drain current              | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>                    | [1] | -   | 50  | A    |
|                           |                            | $V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; <a href="#">Fig. 2</a>                   |     | -   | 50  | A    |
| $I_{DM}$                  | peak drain current         | pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 3</a>  |     | -   | 282 | A    |
| $T_{stg}$                 | storage temperature        |                                                                                              |     | -55 | 175 | °C   |
| $T_j$                     | junction temperature       |                                                                                              |     | -55 | 175 | °C   |
| $T_{sld(M)}$              | peak soldering temperature |                                                                                              |     | -   | 260 | °C   |
| <b>Source-drain diode</b> |                            |                                                                                              |     |     |     |      |
| $I_S$                     | source current             | $T_{mb} = 25\text{ °C}$                                                                      |     | -   | 50  | A    |

N-channel 40 V, 6.7 mΩ, standard level MOSFET in LPAK33 using NextPower-S3 technology

| Symbol                      | Parameter                                    | Conditions                                                                                                                                     |     | Min | Max | Unit |
|-----------------------------|----------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|-----|------|
| $I_{SM}$                    | peak source current                          | pulsed; $t_p \leq 10\ \mu s$ ; $T_{mb} = 25\ ^\circ C$                                                                                         |     | -   | 282 | A    |
| <b>Avalanche ruggedness</b> |                                              |                                                                                                                                                |     |     |     |      |
| $E_{DS(AL)S}$               | non-repetitive drain-source avalanche energy | $I_D = 20\ A$ ; $V_{sup} \leq 40\ V$ ; $R_{GS} = 50\ \Omega$ ; $V_{GS} = 10\ V$ ; $T_{j(init)} = 25\ ^\circ C$ ; unclamped; $t_p = 142\ \mu s$ | [2] | -   | 74  | mJ   |
| $I_{AS}$                    | non-repetitive avalanche current             | $V_{sup} \leq 40\ V$ ; $V_{GS} = 10\ V$ ; $T_{j(init)} = 25\ ^\circ C$ ; $R_{GS} = 50\ \Omega$                                                 | [2] | -   | 50  | A    |

- [1] 50A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [2] Protected by 100% test



9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                         | Conditions             | Min | Typ  | Max  | Unit |
|----------------|---------------------------------------------------|------------------------|-----|------|------|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | <a href="#">Fig. 4</a> | -   | 2.09 | 2.32 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | <a href="#">Fig. 5</a> | -   | 50   | -    | K/W  |
|                |                                                   | <a href="#">Fig. 6</a> | -   | 130  | -    | K/W  |

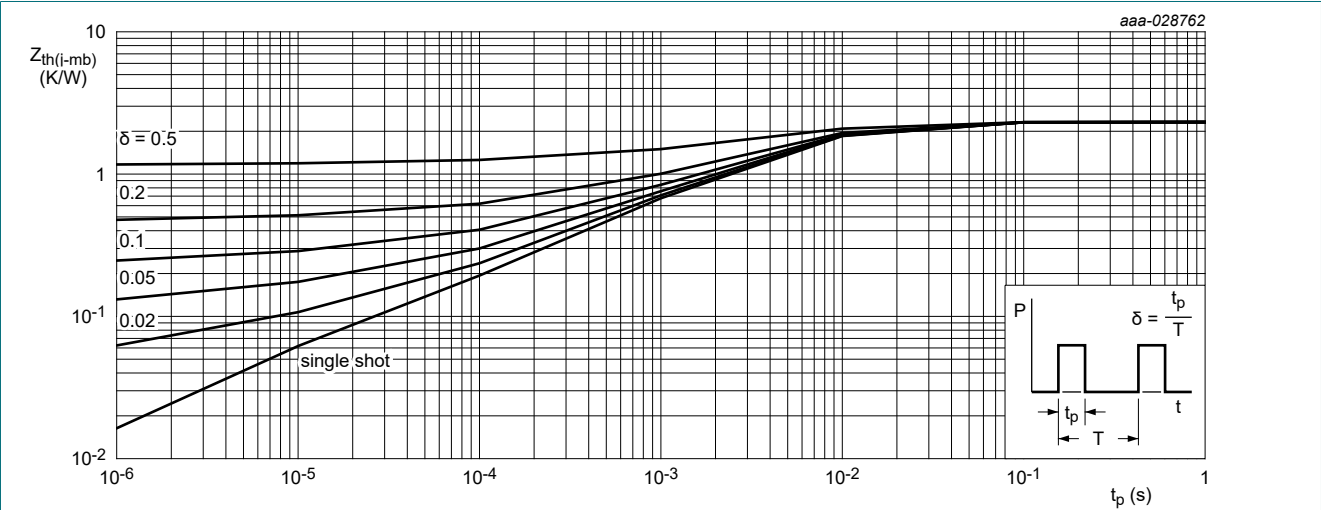


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

Copper area 25.4 mm x 25.4 mm; 70 μm thick on FR4 board

**Fig. 5. PCB layout for thermal resistance from junction to ambient**

70 μm thick copper on FR4 board

**Fig. 6. PCB layout with minimum footprint for thermal resistance from junction to ambient**

10. Characteristics

Table 7. Characteristics

| Symbol                        | Parameter                      | Conditions                                                                             | Min | Typ | Max | Unit |
|-------------------------------|--------------------------------|----------------------------------------------------------------------------------------|-----|-----|-----|------|
| <b>Static characteristics</b> |                                |                                                                                        |     |     |     |      |
| $V_{(BR)DSS}$                 | drain-source breakdown voltage | $I_D = 250\text{ }\mu\text{A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^{\circ}\text{C}$  | 40  | -   | -   | V    |
|                               |                                | $I_D = 250\text{ }\mu\text{A}; V_{GS} = 0\text{ V}; T_j = -55\text{ }^{\circ}\text{C}$ | 36  | -   | -   | V    |

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| Symbol                         | Parameter                                                | Conditions                                                                                                                                 |  | Min | Typ   | Max  | Unit          |
|--------------------------------|----------------------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------|--|-----|-------|------|---------------|
| $V_{GS(th)}$                   | gate-source threshold voltage                            | $I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ }^\circ\text{C}$                                                               |  | 2.4 | 3     | 3.6  | V             |
| $\Delta V_{GS(th)}/\Delta T$   | gate-source threshold voltage variation with temperature | $25 \text{ }^\circ\text{C} \leq T_j \leq 150 \text{ }^\circ\text{C}$                                                                       |  | -   | -6.24 | -    | mV/K          |
| $I_{DSS}$                      | drain leakage current                                    | $V_{DS} = 32 \text{ V}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$                                                       |  | -   | 0.004 | 1    | $\mu\text{A}$ |
|                                |                                                          | $V_{DS} = 32 \text{ V}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 125 \text{ }^\circ\text{C}$                                                      |  | -   | 0.3   | -    | $\mu\text{A}$ |
| $I_{GSS}$                      | gate leakage current                                     | $V_{GS} = 20 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$                                                       |  | -   | 2     | 100  | nA            |
|                                |                                                          | $V_{GS} = -20 \text{ V}$ ; $V_{DS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$                                                      |  | -   | 2     | 100  | nA            |
| $R_{DS(on)}$                   | drain-source on-state resistance                         | $V_{GS} = 10 \text{ V}$ ; $I_D = 20 \text{ A}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>                               |  | -   | 5.7   | 6.7  | mΩ            |
|                                |                                                          | $V_{GS} = 10 \text{ V}$ ; $I_D = 20 \text{ A}$ ; $T_j = 175 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>                              |  | -   | -     | 13   | mΩ            |
| $R_G$                          | gate resistance                                          | $f = 1 \text{ MHz}$ ; $T_j = 25 \text{ }^\circ\text{C}$                                                                                    |  | 0.3 | 0.8   | 1.9  | Ω             |
| <b>Dynamic characteristics</b> |                                                          |                                                                                                                                            |  |     |       |      |               |
| $Q_{G(tot)}$                   | total gate charge                                        | $I_D = 20 \text{ A}$ ; $V_{DS} = 20 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>               |  | 10  | 16    | 22   | nC            |
|                                |                                                          | $I_D = 0 \text{ A}$ ; $V_{DS} = 0 \text{ V}$ ; $V_{GS} = 10 \text{ V}$                                                                     |  | -   | 8.7   | -    | nC            |
| $Q_{GS}$                       | gate-source charge                                       | $I_D = 20 \text{ A}$ ; $V_{DS} = 20 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>               |  | 3.3 | 5.5   | 8.3  | nC            |
| $Q_{GS(th)}$                   | pre-threshold gate-source charge                         |                                                                                                                                            |  | 2   | 3.4   | 5.1  | nC            |
| $Q_{GS(th-pl)}$                | post-threshold gate-source charge                        |                                                                                                                                            |  | 1.3 | 2.1   | 3.2  | nC            |
| $Q_{GD}$                       | gate-drain charge                                        |                                                                                                                                            |  | 0.7 | 2.4   | 4.8  | nC            |
| $V_{GS(pl)}$                   | gate-source plateau voltage                              | $I_D = 20 \text{ A}$ ; $V_{DS} = 20 \text{ V}$ ; <a href="#">Fig. 12</a> ; <a href="#">Fig. 13</a>                                         |  | -   | 4.7   | -    | V             |
| $C_{iss}$                      | input capacitance                                        | $V_{DS} = 20 \text{ V}$ ; $V_{GS} = 0 \text{ V}$ ; $f = 1 \text{ MHz}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 14</a>       |  | 762 | 1173  | 1642 | pF            |
| $C_{oss}$                      | output capacitance                                       |                                                                                                                                            |  | 302 | 465   | 651  | pF            |
| $C_{rss}$                      | reverse transfer capacitance                             |                                                                                                                                            |  | 16  | 55    | 121  | pF            |
| $t_{d(on)}$                    | turn-on delay time                                       | $V_{DS} = 20 \text{ V}$ ; $R_L = 1 \text{ } \Omega$ ; $V_{GS} = 10 \text{ V}$ ; $R_{G(ext)} = 5 \text{ } \Omega$                           |  | -   | 7.6   | -    | ns            |
| $t_r$                          | rise time                                                |                                                                                                                                            |  | -   | 6.2   | -    | ns            |
| $t_{d(off)}$                   | turn-off delay time                                      |                                                                                                                                            |  | -   | 13.2  | -    | ns            |
| $t_f$                          | fall time                                                |                                                                                                                                            |  | -   | 6.2   | -    | ns            |
| $Q_{oss}$                      | output charge                                            | $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 20 \text{ V}$ ; $f = 1 \text{ MHz}$ ; $T_j = 25 \text{ }^\circ\text{C}$                                 |  | -   | 13.5  | -    | nC            |
| <b>Source-drain diode</b>      |                                                          |                                                                                                                                            |  |     |       |      |               |
| $V_{SD}$                       | source-drain voltage                                     | $I_S = 20 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 15</a>                                |  | -   | 0.85  | 1    | V             |
| $t_{rr}$                       | reverse recovery time                                    | $I_S = 20 \text{ A}$ ; $dI_S/dt = -100 \text{ A}/\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 20 \text{ V}$ ; <a href="#">Fig. 16</a> |  | -   | 23    | -    | ns            |
| $Q_r$                          | recovered charge                                         |                                                                                                                                            |  | -   | 17    | -    | nC            |
| $t_a$                          | reverse recovery rise time                               |                                                                                                                                            |  | -   | 14    | -    | ns            |
| $t_b$                          | reverse recovery fall time                               |                                                                                                                                            |  | -   | 9     | -    | ns            |

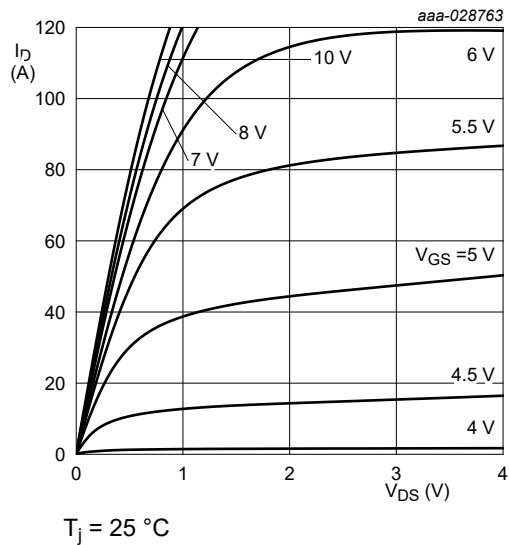


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

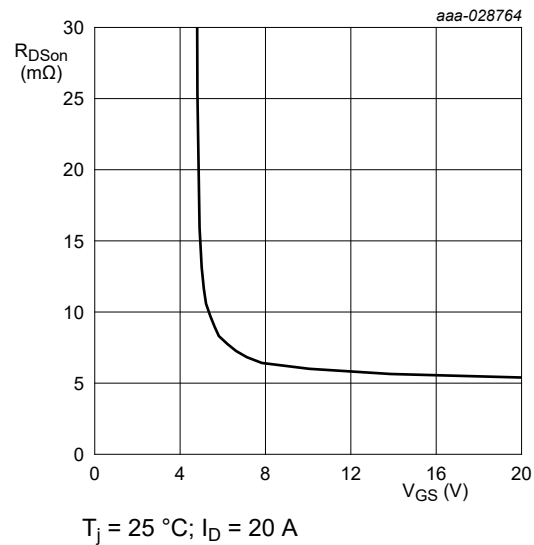


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

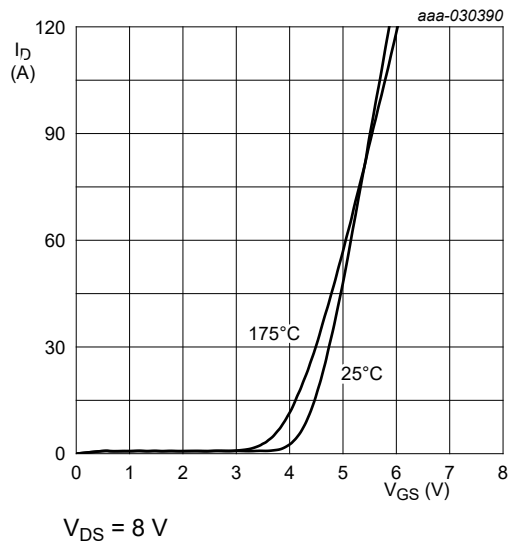


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

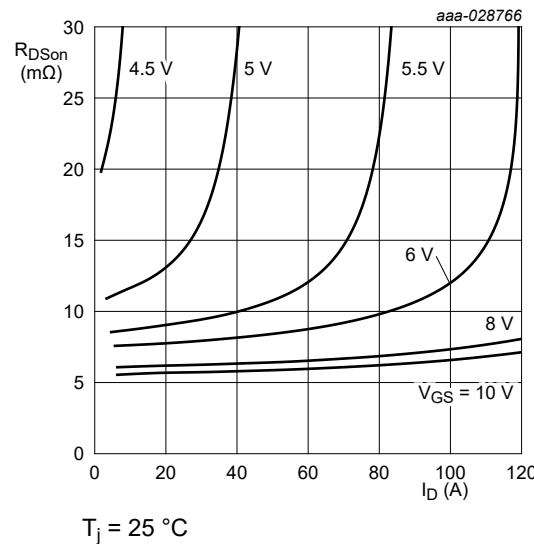


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

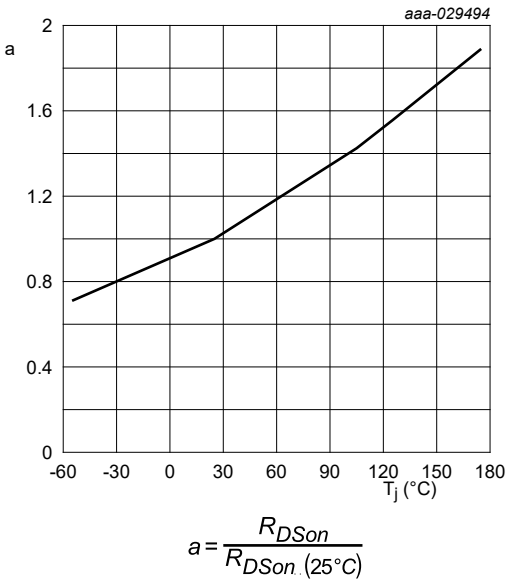


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

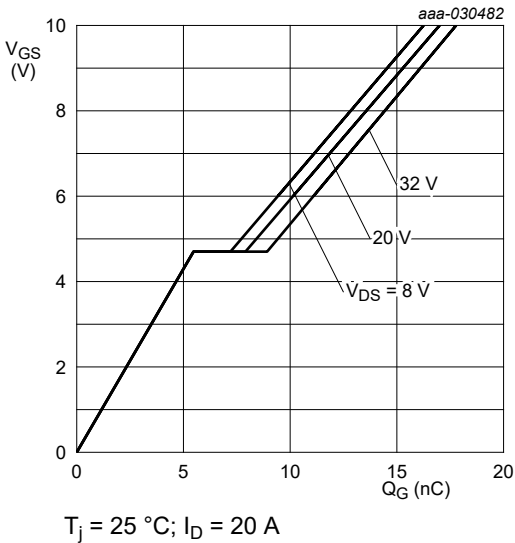


Fig. 12. Gate-source voltage as a function of gate charge; typical values

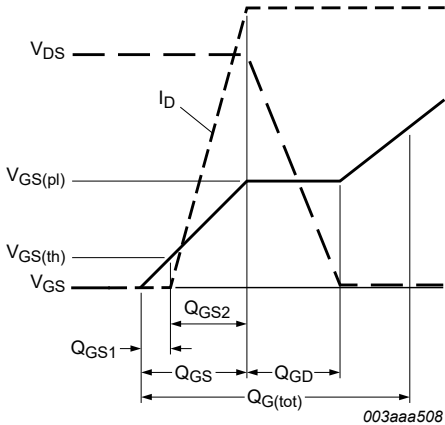


Fig. 13. Gate charge waveform definitions

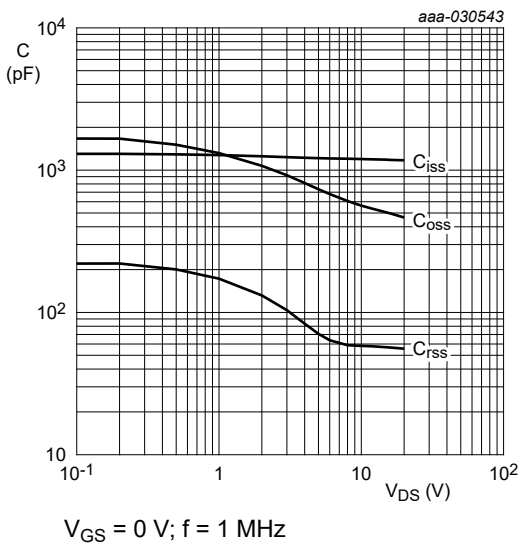
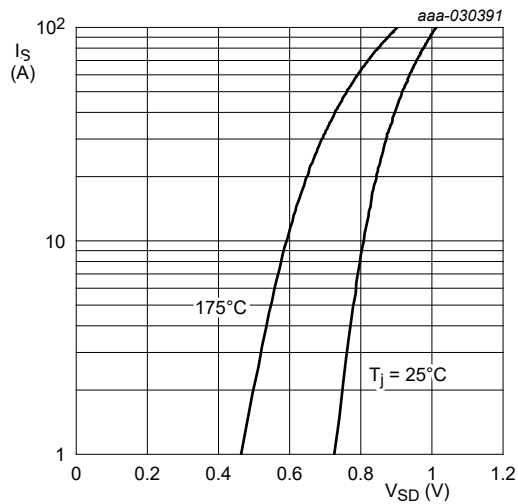


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0\text{ V}$

Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

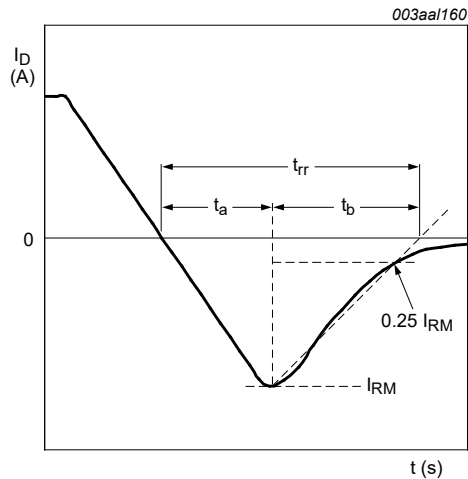


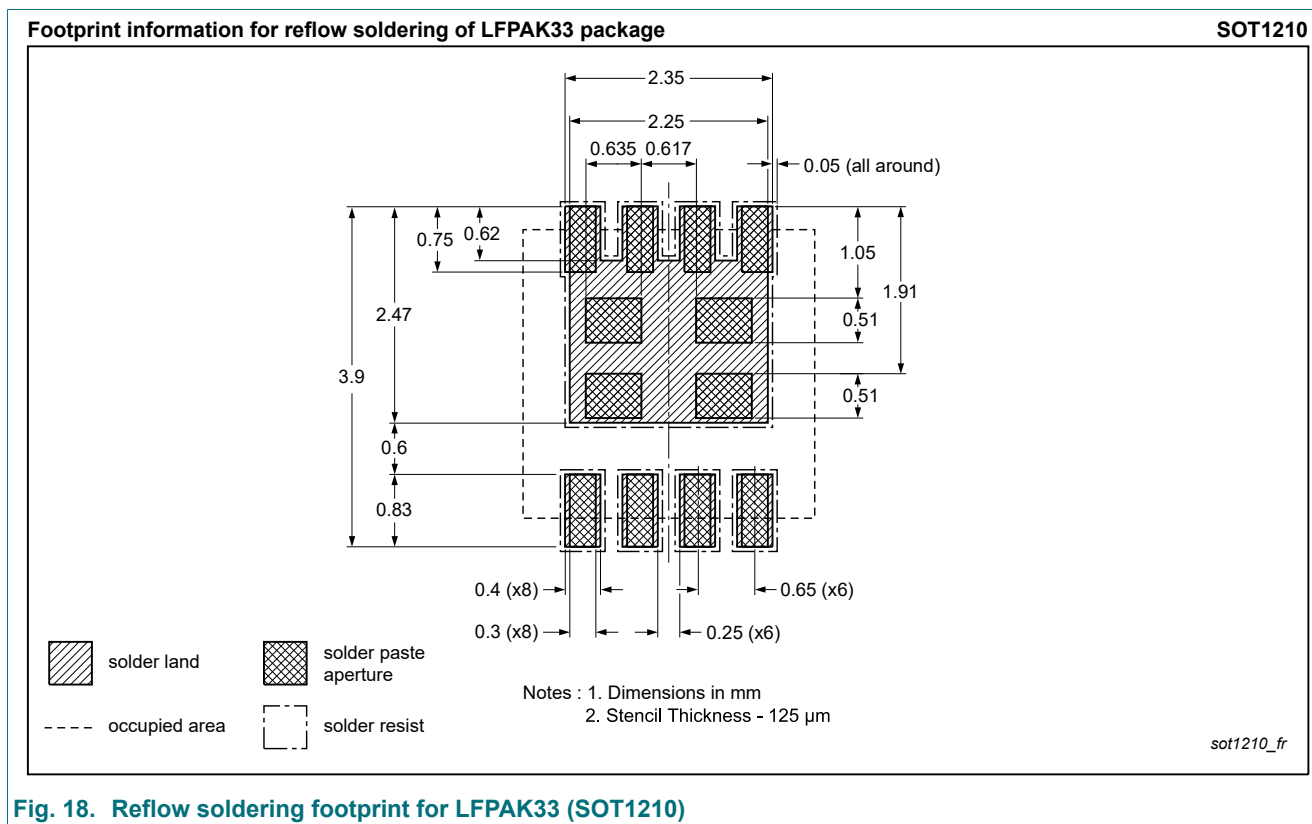
Fig. 16. Reverse recovery timing definition

11. Package outline



Fig. 17. Package outline LPAK33 (SOT1210)

## 12. Soldering



## 13. Legal information

### Data sheet status

| Document status<br>[1][2]      | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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